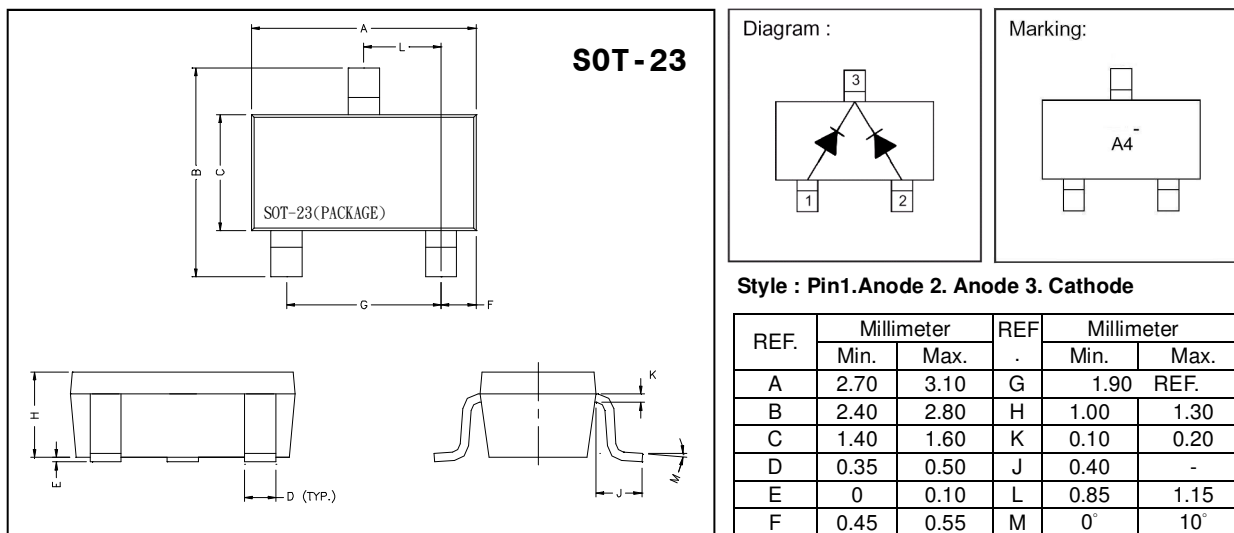


GBAV70

Description

The GBAV70 consists of two diodes in a plastic surface mount package. The diodes are connected in series and the unit is designed for high-speed switching application in hybrid thick and thin-film circuits.

Package Dimensions



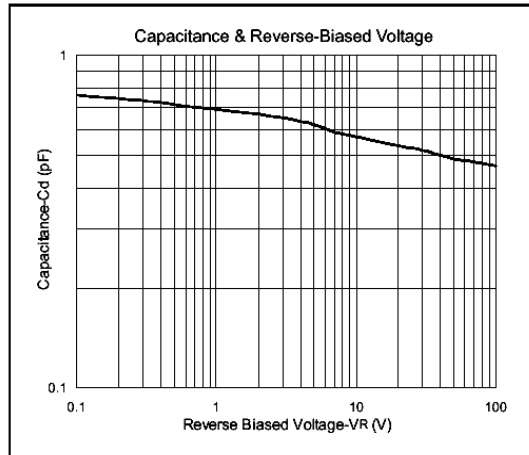
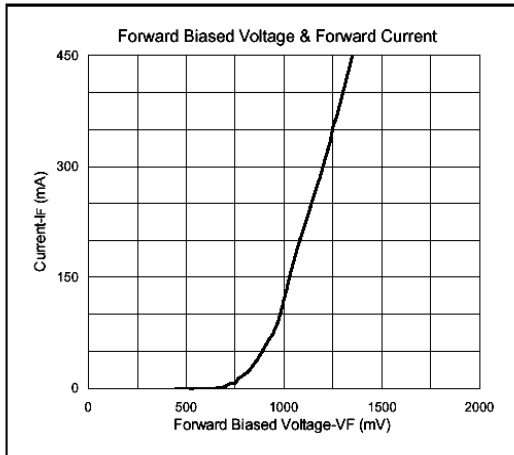
Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Ratings	Unit
Junction Temperature	T _j	+150	°C
Storage Temperature	T _{stg}	-65~+150	°C
Reverse Voltage		80	V
Forward Current		200	mA
Repetitive Forward Current		500	mA
Total Power Dissipation	PD	225	mW

Characteristics at Ta = 25°C

Characteristic	Symbol	Min.	Max.	Unit	Test Conditions
Reverse Breakdown Voltage	V(BR)	80	-	V	IR=100uA
Forward Voltage	VF(1)	-	715	mV	IF=1mA
	VF(2)	-	855	mV	IF=10mA
	VF(3)	-	1100	mV	IF=50mA
	VF(4)	-	1300	mV	IF=100mA
Reverse Current	IR	-	5	uA	VR=80V
Total Capacitance	CT		1.5	pF	VR=0, f=1MHz
Reverse Recovery Time	T _{rr}	-	15	nS	IF=IR=10mA, RL=100Ω measured at IR=1Ma, VR=5V

Characteristics Curve



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Head Office And Factory:

- **Taiwan:** No. 17-1 Tatung Rd. Fu Kou Hsin-Chu Industrial Park, Hsin-Chu, Taiwan, R. O. C.
TEL : 886-3-597-7061 FAX : 886-3-597-9220, 597-0785
- **China:** (201203) No.255, Jang-Jiang Tsai-Lueng RD. , Pu-Dung-Hsin District, Shang-Hai City, China
TEL : 86-21-5895-7671 FAX : 86-21-38950165

